

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-16. (Canceled).

17. (Original) A method of forming a silicon thin-film which comprises:  
a step of forming on one or more parts of a liquid arranging surface for arranging liquid on a first substrate an active region and inactive region for CVD;  
a step of arranging on said liquid arranging surface liquid which contains a silicide comprising ring silane and/or a derivative thereof, said ring silane comprising silicon and hydrogen;  
a step of arranging a thin-film-forming surface for forming a second substrate to be set facing the liquid arranging surface of said first substrate; and  
a step of vaporizing silicide from said liquid arranged on said liquid arranging surface of said first substrate and supplying said silicide to said thin-film-forming surface of said second substrate to selectively deposit a silicon thin-film.

18. (Original) A method of forming a silicon thin-film according to claim 17, wherein a solution in which cyclopentasilane and/or silylcyclopentasilane are/is dissolved in an organic solvent is used as said liquid containing silicide.

19. (Currently Amended) A method of forming a silicon thin-film according to claim 17, wherein said step of forming an active region and inactive region for CVD comprises:

a step of, when R is a fluoroalkyl group in which hydrogen on an end side of an alkyl group is substituted with fluorine and X is an alkoxy group or a halogen group, forming a self-assembled film on said ~~thin-film-forming~~ liquid arranging surface on which a hydroxyl group exists, using a silane derivative indicated by the general formula  $\text{RSiX}_3$ ; and

a step of performing a physical treatment of said self-assembled film and removing a part of said self-assembled film which becomes an active region for CVD in order to form an active region and inactive region for chemical vapor disposition.

20. (Original) A method of forming a silicon thin-film according to claim 19, wherein said step of removing said self-assembled film performs ultraviolet ray irradiation through a photomask or electron beam irradiation to a necessary part as said physical treatment.